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Erratum: "Mechanically induced Si layer transfer in hydrogen implanted Si wafers" [Appl. Phys. Lett. 76, 2370 (2000)] FREE

K. Henttinen; I. Suni; S. S. Lau



Appl. Phys. Lett. 77, 310 (2000)
<https://doi.org/10.1063/1.126960>



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Erratum: “Mechanically induced Si layer transfer in hydrogen implanted Si wafers” [Appl. Phys. Lett. 76, 2370 (2000)]

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Due to authors mistake, Ref. 3 of the letter was published incorrectly. The name of the first author in this reference, Q.-Y. Tong, was omitted. The correct reference should read: ³Q.-Y. Tong and U. Gösele, *Semiconductor Wafer Bonding*, Electrochemical Society Series (Wiley, New York, 1999), p. 66.

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